

## AMENDMENTS TO THE CLAIMS

1-14. (cancelled).

15. (currently amended) A wafer polishing system comprising:  
a first chemical-mechanical polishing station having a polishing portion;  
a source of an oxidizer-free medium in communication with said polishing portion; and  
a source of an oxidizing medium in communication with said polishing portion;  
wherein said source of an oxidizer-free medium and said source of an oxidizing medium are maintained separately and wherein said source of an oxidizer-free medium is utilized by said polishing station prior to said source of an oxidizing medium to polish a surface of a wafer.

16. (original) The wafer polishing system of claim 15, further comprising:  
a second polishing station; and  
a transfer mechanism adapted to move said wafer from said first polishing station to said second polishing station.

17. (currently amended) A wafer polishing system comprising:  
a first polishing station adapted to polish a surface of a wafer in the presence of an oxidizer-free medium;  
a source of an oxidizer-free medium in communication with said first polishing station;  
a second polishing station adapted to polish said surface of said wafer in the presence of an oxidizing medium;  
a source of an oxidizing medium ~~slurry~~ in communication with said second polishing station; and  
a transfer mechanism adapted to move a wafer from said first polishing station to said second polishing station.

18. (original) The wafer polishing system of claim 17, wherein said source of oxidizing solution is also in communication with said first polishing station.

19. (original) The wafer polishing system of claim 17, further comprising:  
a second source of an oxidizing medium in communication with said first polishing station.
20. (original) The wafer polishing station of claim 17, wherein said oxidizer-free medium comprises an oxidizer-free slurry, and said oxidizing medium comprises an oxidizing slurry.
21. (previously presented) A wafer polishing system comprising:  
a plurality of polishing stations;  
a delivery system for supplying an oxidizer-free medium to at least one of said polishing stations to polish a surface of a wafer;  
a delivery system for supplying an oxidizing medium to at least one of said polishing stations to polish said wafer surface;  
a transfer mechanism adapted to move said wafer among said plurality of polishing stations;  
wherein said oxidizer-free medium polishes the wafer surface prior to the oxidizing medium.
22. (previously presented) The wafer polishing system of claim 21, wherein said oxidizer-free medium and said oxidizing medium are delivered to the same polishing station.
23. (previously presented) The wafer polishing system of claim 21, wherein said oxidizer-free medium and said oxidizing medium are delivered to different polishing stations.